



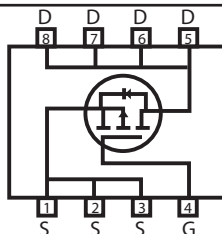
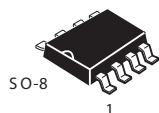
## P-Channel Enhancement Mode MOSFET

### PRODUCT SUMMARY

V <sub>DSS</sub>	I <sub>D</sub>	R <sub>DS(ON)</sub> (m $\Omega$ ) Max
-30V	-10A	13 @ V <sub>GS</sub> = -20V
		14 @ V <sub>GS</sub> = -10V
		24 @ V <sub>GS</sub> = -4.5V

### FEATURES

- Super high dense cell design for low R<sub>DS(ON)</sub>.
- Rugged and reliable.
- Surface Mount Package.



### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	- 30	V
Gate-Source Voltage	V <sub>GS</sub>	±25	V
Drain Current-Continuous <sup>a</sup> @ T <sub>J</sub> =125°C -Pulsed <sup>b</sup>	I <sub>D</sub>	- 10	A
	I <sub>DM</sub>	- 50	A
Drain-Source Diode Forward Current <sup>a</sup>	I <sub>S</sub>	-1.7	A
Maximum Power Dissipation <sup>a</sup>	P <sub>D</sub>	2.5	W
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C

### THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient <sup>a</sup>	R $\theta$ JA	50	°C/W
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## ELECTRICAL CHARACTERISTICS (TA =25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ <sup>c</sup>	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-30			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-24V, V <sub>GS</sub> = 0V			-1	uA
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>GS</sub> =±25V, V <sub>DS</sub> =0V			±100	nA
ON CHARACTERISTICS <sup>b</sup>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> = -250uA	-1	-1.8	-2.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-20V, I <sub>D</sub> =-10A		9	13	m-ohm
		V <sub>GS</sub> =-10V, I <sub>D</sub> =-10A		10	14	m-ohm
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-10A		15	24	m-ohm
On-State Drain Current	I <sub>D(ON)</sub>	V <sub>DS</sub> = -5V, V <sub>GS</sub> = -10V	30			A
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = -5V, I <sub>D</sub> =-10A		20		S
DYNAMIC CHARACTERISTICS <sup>c</sup>						
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V f =1.0MHz		2963		pF
Output Capacitance	C <sub>OSS</sub>			641		pF
Reverse Transfer Capacitance	C <sub>RSS</sub>			276		pF
SWITCHING CHARACTERISTICS <sup>c</sup>						
Turn-On Delay Time	t <sub>D(ON)</sub>	V <sub>DD</sub> = -15V R <sub>L</sub> =1.25ohm V <sub>GS</sub> = -10V R <sub>GEN</sub> =6ohm		4.9		ns
Rise Time	t <sub>r</sub>			8.8		ns
Turn-Off Delay Time	t <sub>D(OFF)</sub>			27.1		ns
Fall Time	t <sub>f</sub>			15.5		ns
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = -15V, I <sub>D</sub> = -10A, V <sub>GS</sub> = -10V		60.5		nC
Gate-Source Charge	Q <sub>gs</sub>			8.3		nC
Gate-Drain Charge	Q <sub>gd</sub>			13.7		nC

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## ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ <sup>c</sup>	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS <sup>b</sup>						
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1.7A		-0.73	-1.2	V

### Notes

- a.Surface Mounted on FR4 Board, t ≤ 10sec.
- b.Pulse Test:Pulse Width ≤ 300us, Duty Cycle ≤ 2%.
- c.Guaranteed by design, not subject to production testing.

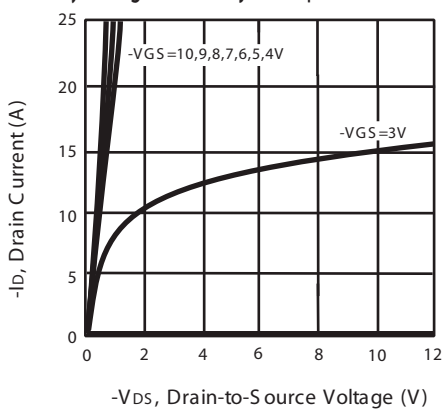


Figure 1. Output Characteristics

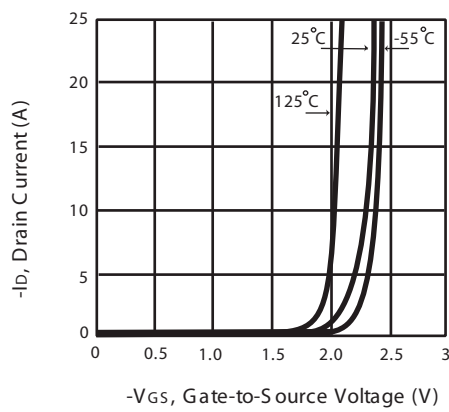


Figure 2. Transfer Characteristics

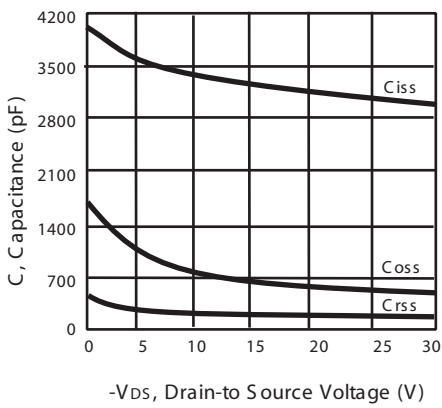


Figure 3. Capacitance

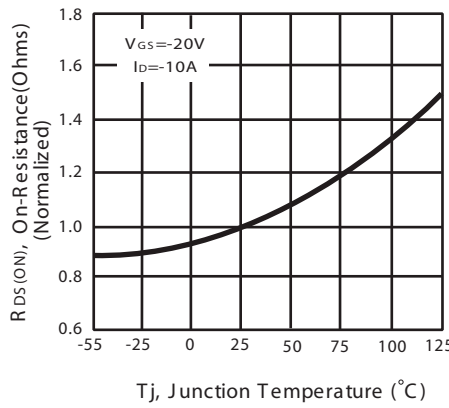


Figure 4. On-Resistance Variation with Temperature

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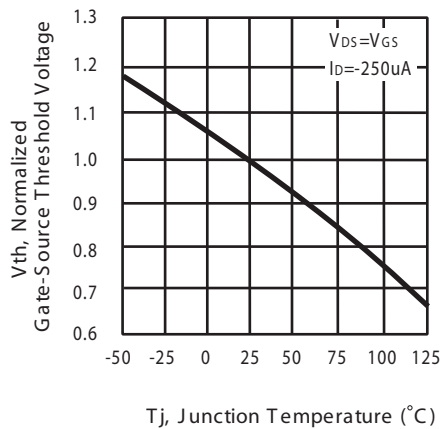


Figure 5. Gate Threshold Variation with Temperature

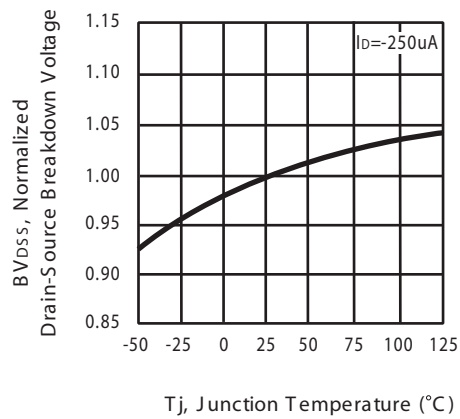


Figure 6. Breakdown Voltage Variation with Temperature

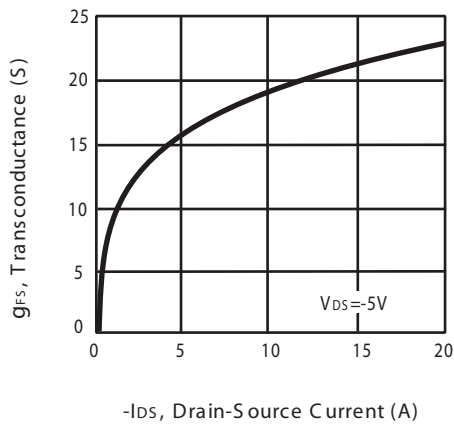


Figure 7. Transconductance Variation with Drain Current

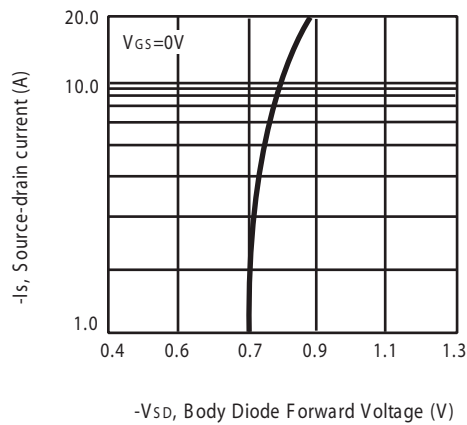


Figure 8. Body Diode Forward Voltage Variation with Source Current

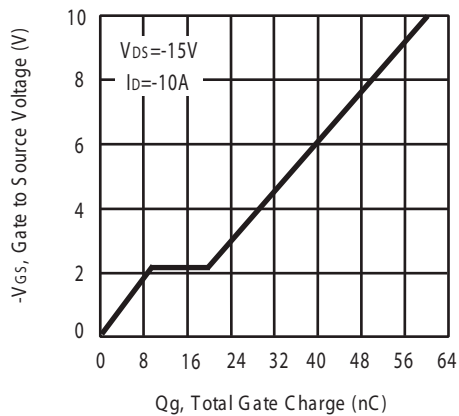


Figure 9. Gate Charge

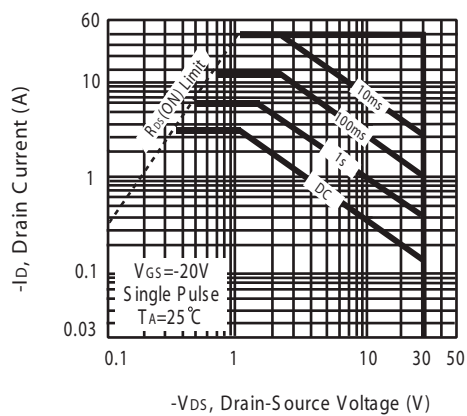


Figure 10. Maximum Safe Operating Area

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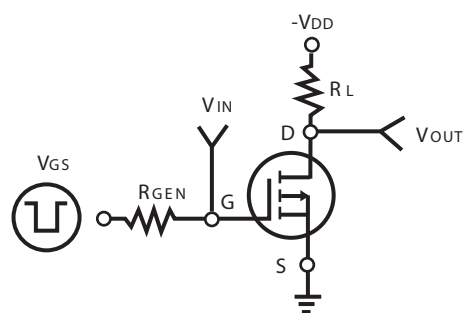


Figure 11. Switching Test Circuit

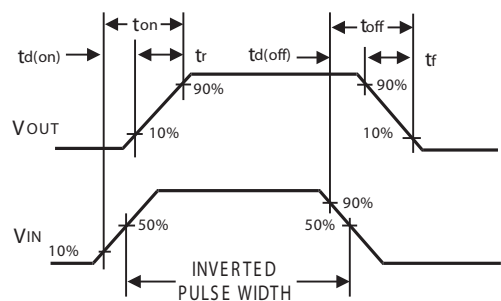


Figure 12. Switching Waveforms

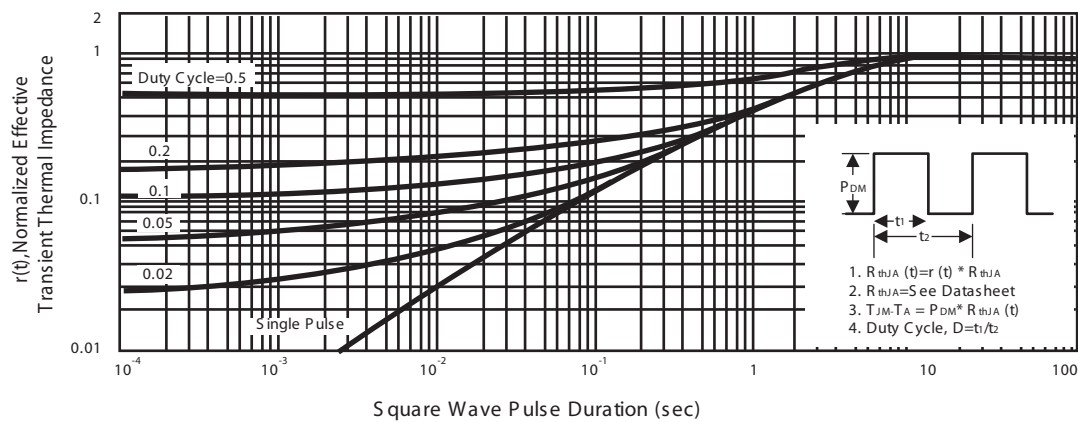
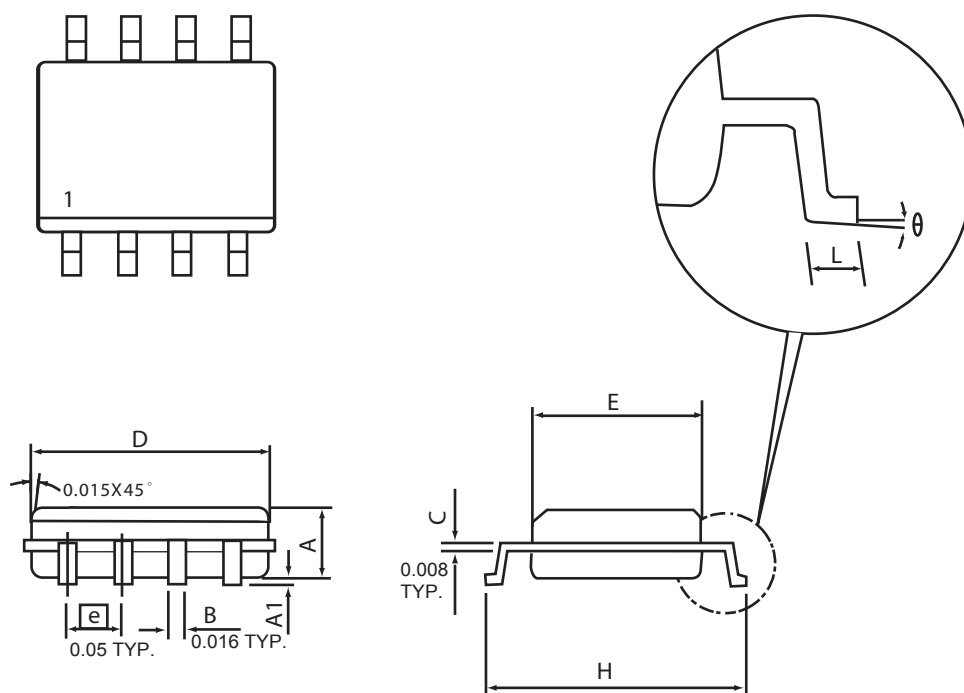


Figure 13. Normalized Thermal Transient Impedance Curve

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## PACKAGE OUTLINE DIMENSIONS

### SO-8

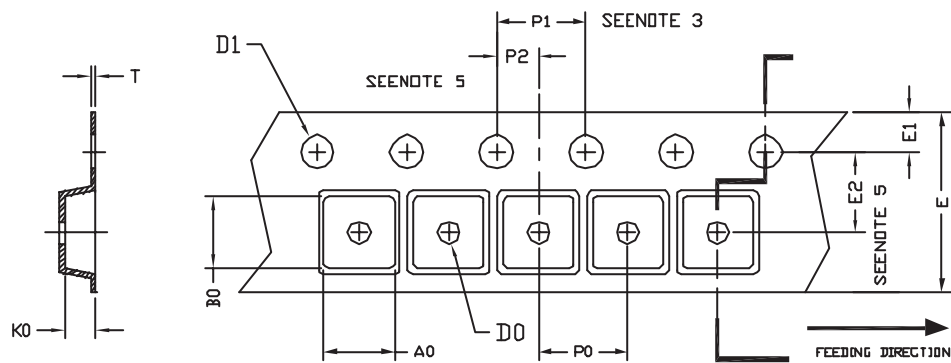


SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.35	1.75	0.053	0.069
A1	0.10	0.25	0.004	0.010
D	4.80	4.98	0.189	0.196
E	3.81	3.99	0.150	0.157
H	5.79	6.20	0.228	0.244
L	0.41	1.27	0.016	0.050
$\theta$	0°	8°	0°	8°

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## SO-8 Tape and Reel Data

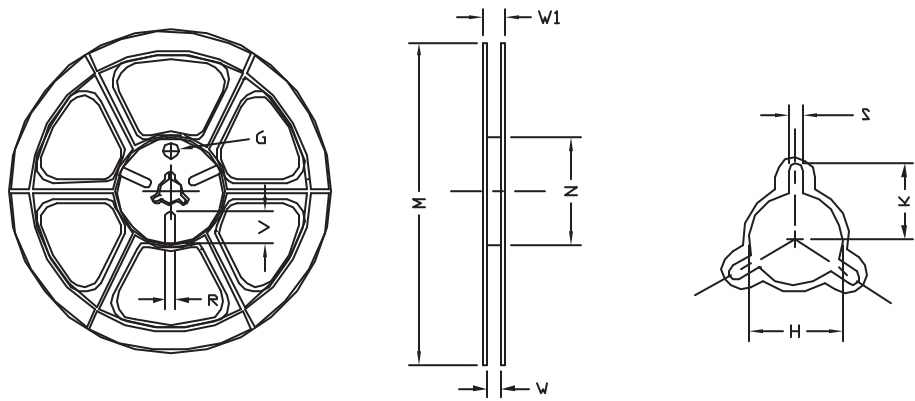
### SO-8 Carrier Tape



unit:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SOP 8N 150mil	6.40	5.20	2.10	$\phi 1.5$ (MIN)	$\phi 1.5$ + 0.1 - 0.0	12.0 $\pm 0.3$	1.75	5.5 $\pm 0.05$	8.0	4.0	2.0 $\pm 0.05$	0.3 $\pm 0.05$

### SO-8 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
12 mm	$\phi 330$	330 $\pm 1$	62 $\pm 1.5$	12.4 + 0.2	16.8 - 0.4	$\phi 12.75$ + 0.15	---	2.0 $\pm 0.15$	---	---	---